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The original Supporting Information file contained incorrect data in Table S1. Please see correct values below.

Table S1. TFT Characteristics of an Aging Device

aging time (h)	threshold voltage (V_{th})	saturation mobility ($cm^2\ V^{-1}\ s^{-1}$)	on current (A)	off current (A)	on/off ratio	subthreshold swing (V/decade)
0	6.23	1.18	8.94×10^{-4}	2.00×10^{-7}	4.48×10^{3}	4.2
0.5	3.41	0.75	6.46×10^{-4}	7.75×10^{-8}	8.34×10^{3}	3.5
2	5.47	0.75	5.75×10^{-4}	4.27×10^{-8}	1.35×10^{4}	2.6
6	7.06	0.76	5.39×10^{-4}	1.80×10^{-8}	2.99×10^{4}	1.9
12	6.57	0.70	4.99×10^{-4}	1.46×10^{-8}	3.42×10^{4}	1.8

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